



PMZ370UNE

30 V, N-channel Trench MOSFET

14 May 2014

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Leadless ultra small SMD plastic package: 1.0 × 0.6 × 0.48 mm

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

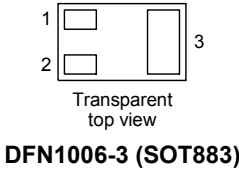
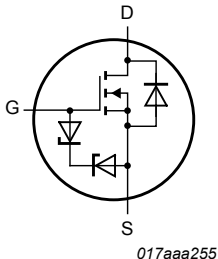
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_J = 25\text{ }^{\circ}\text{C}$		-	-	30	V
V_{GS}	gate-source voltage			-8	-	8	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	-	-	900	mA
Static characteristics							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 500\text{ mA}; T_J = 25\text{ }^{\circ}\text{C}$		-	370	490	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 Transparent top view DFN1006-3 (SOT883)	 017aaa255
2	S	source		
3	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMZ370UNE	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883

7. Marking

Table 4. Marking codes

Type number	Marking code
PMZ370UNE	ZM

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ }^{\circ}\text{C}$		-	30	V
V_{GS}	gate-source voltage			-8	8	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	-	900	mA
		$V_{GS} = 4.5\text{ V}; T_{amb} = 100\text{ }^{\circ}\text{C}$	[1]	-	560	mA
I_{DM}	peak drain current	$T_{amb} = 25\text{ }^{\circ}\text{C}$; single pulse; $t_p \leq 10\text{ }\mu\text{s}$		-	3.6	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ }^{\circ}\text{C}$	[2]	-	360	mW
			[1]	-	715	mW
		$T_{sp} = 25\text{ }^{\circ}\text{C}$		-	2700	mW
T_j	junction temperature			-55	150	$^{\circ}\text{C}$
T_{amb}	ambient temperature			-55	150	$^{\circ}\text{C}$
T_{stg}	storage temperature			-65	150	$^{\circ}\text{C}$
Source-drain diode						
I_S	source current	$T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	-	680	mA
ESD maximum rating						
V_{ESD}	electrostatic discharge voltage	HBM	[3]	-	2000	V

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm^2 .

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

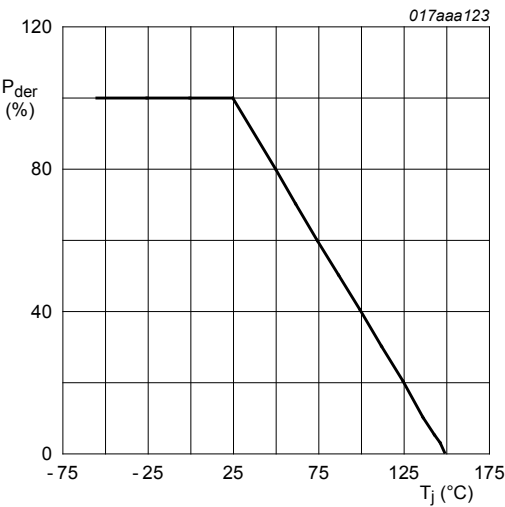


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

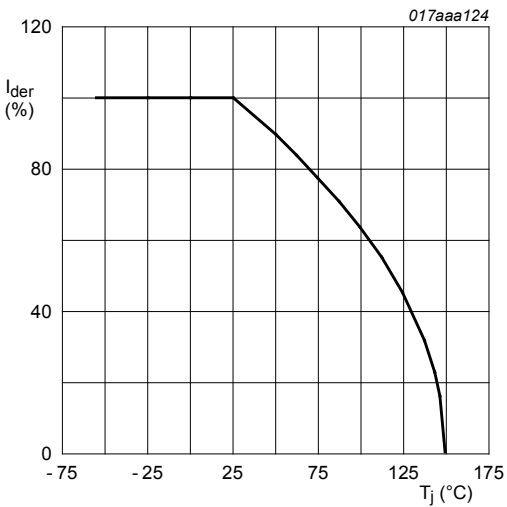


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

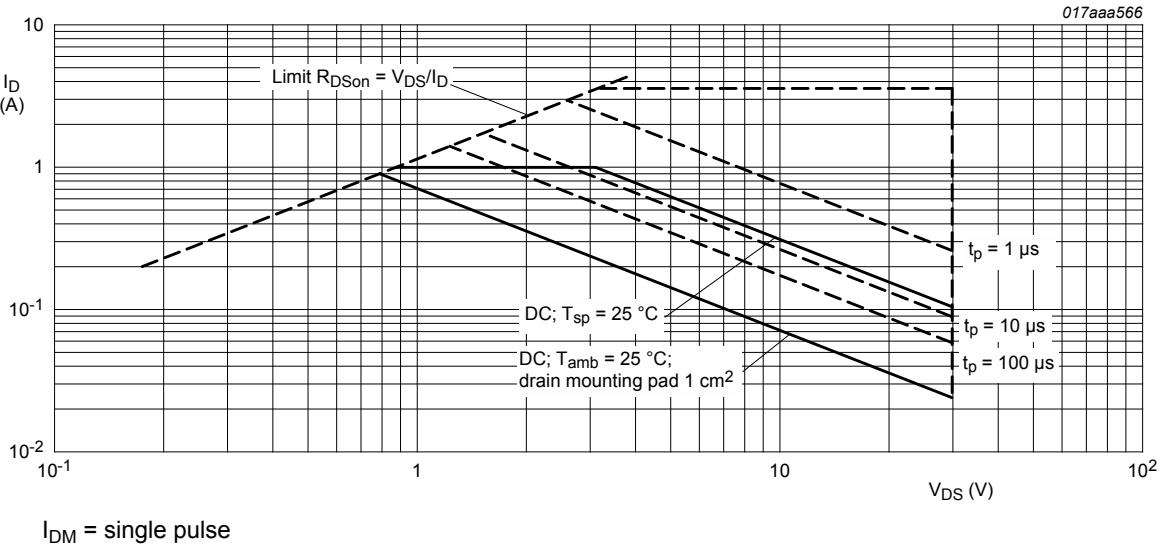


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	305	360	K/W
			[2]	-	150	175	K/W

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	40	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

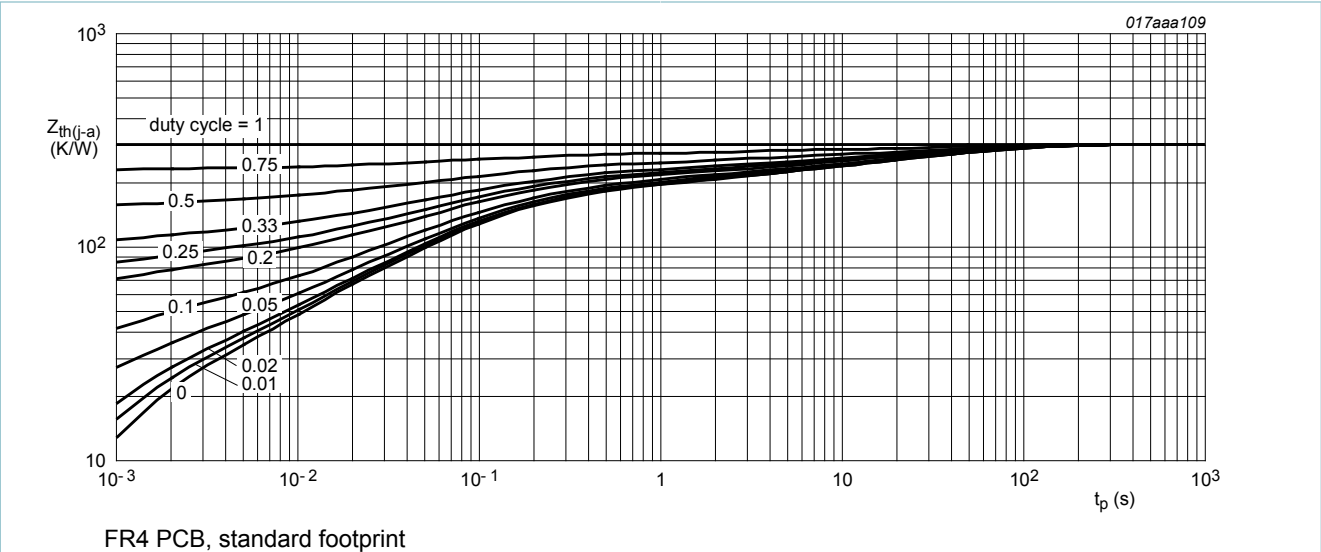


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

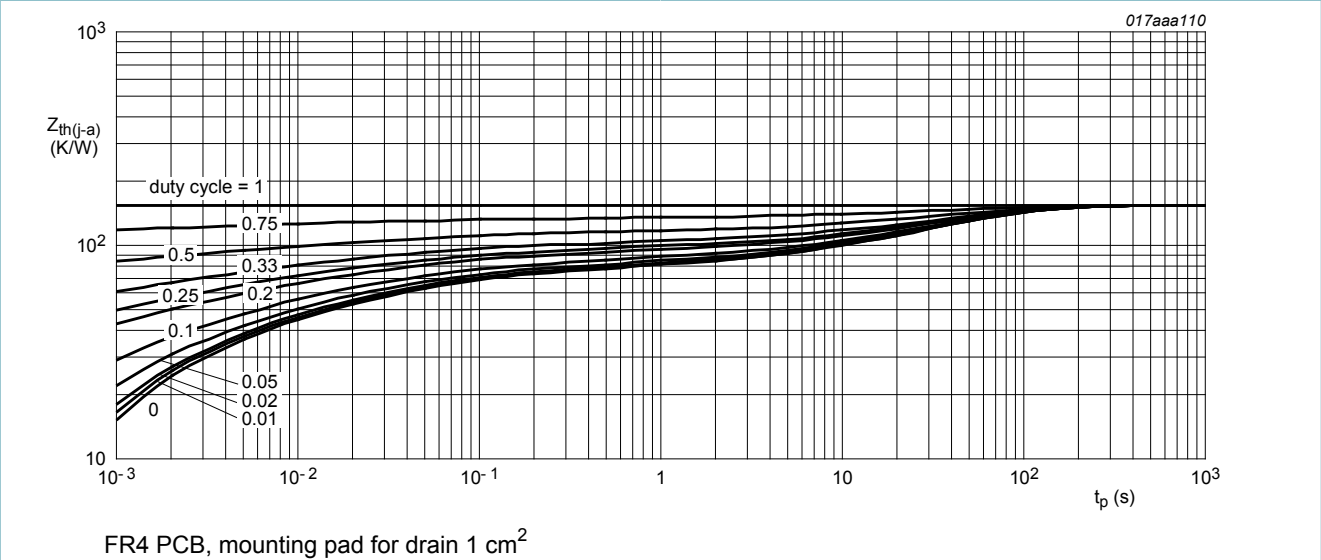


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C		30	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C		0.5	0.77	1.05	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C		-	-	1	μA
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 150 °C		-	-	10	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C		-	-	3	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C		-	-	3	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C		-	-	0.5	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C		-	-	0.5	μA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 500 mA; T _j = 25 °C		-	370	490	mΩ
		V _{GS} = 4.5 V; I _D = 500 mA; T _j = 150 °C		-	650	860	mΩ
		V _{GS} = 2.5 V; I _D = 400 mA; T _j = 25 °C		-	470	750	mΩ
		V _{GS} = 1.8 V; I _D = 100 mA; T _j = 25 °C		-	630	1300	mΩ
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 200 mA; T _j = 25 °C		-	1580	-	mS
Dynamic characteristics							
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 500 mA; V _{GS} = 4.5 V; T _j = 25 °C		-	0.77	1.16	nC
Q _{GS}	gate-source charge			-	0.15	-	nC
Q _{GD}	gate-drain charge			-	0.16	-	nC
C _{iss}	input capacitance	V _{DS} = 25 V; f = 1 MHz; V _{GS} = 0 V; T _j = 25 °C		-	52	78	pF
C _{oss}	output capacitance			-	9	-	pF
C _{rss}	reverse transfer capacitance			-	3	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; R _L = 250 Ω; V _{GS} = 4.5 V; R _{G(ext)} = 6 Ω; T _j = 25 °C		-	11	22	ns
t _r	rise time			-	9	-	ns
t _{d(off)}	turn-off delay time			-	54	108	ns
t _f	fall time			-	27	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 300 mA; V _{GS} = 0 V; T _j = 25 °C		0.48	0.76	1.2	V

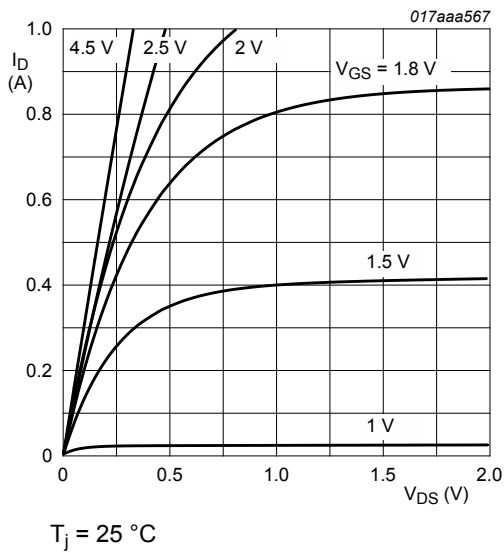


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

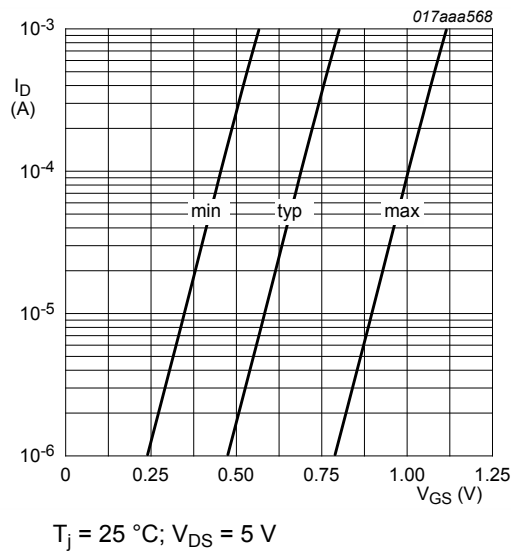


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

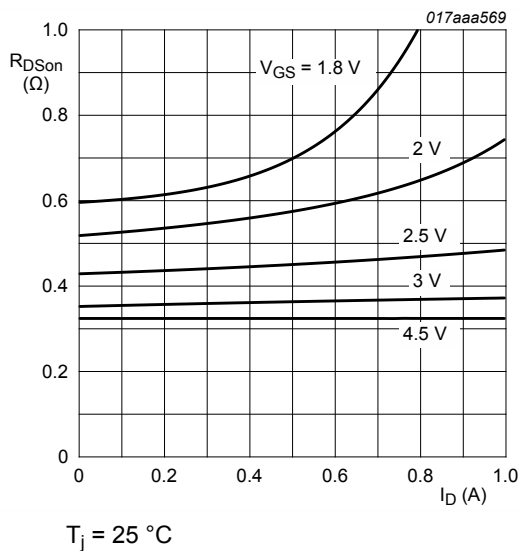


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

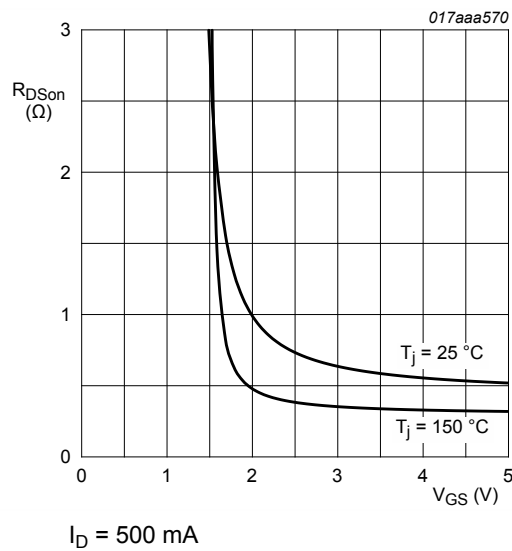


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

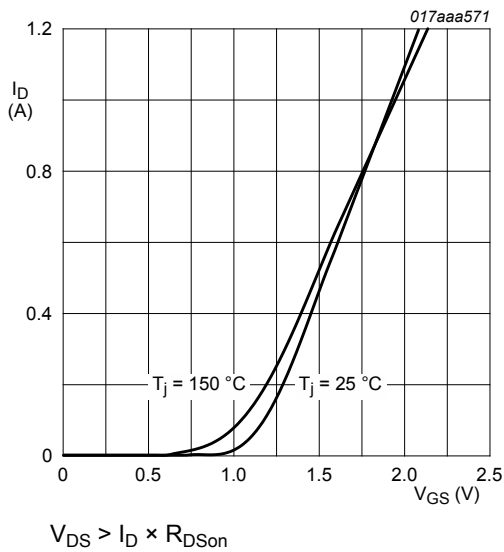


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

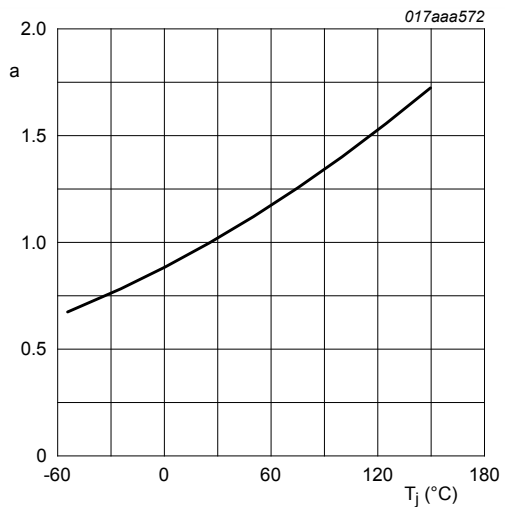


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}\text{C})}}$$

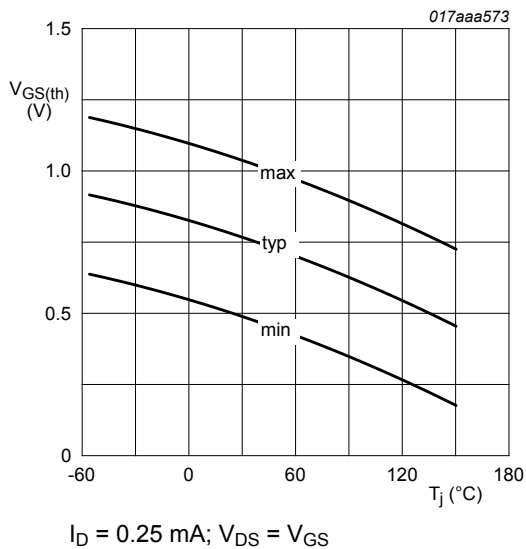


Fig. 12. Gate-source threshold voltage as a function of junction temperature

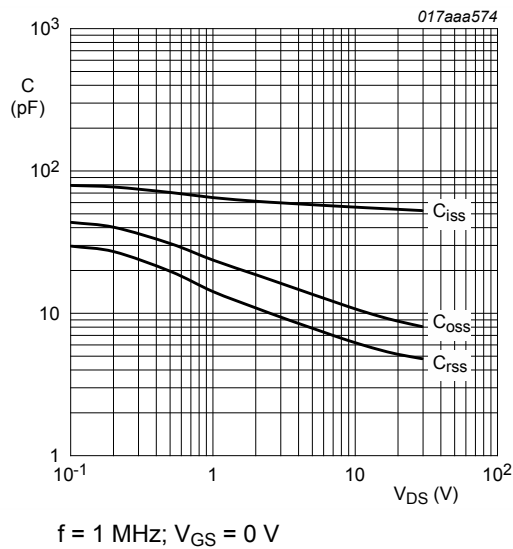
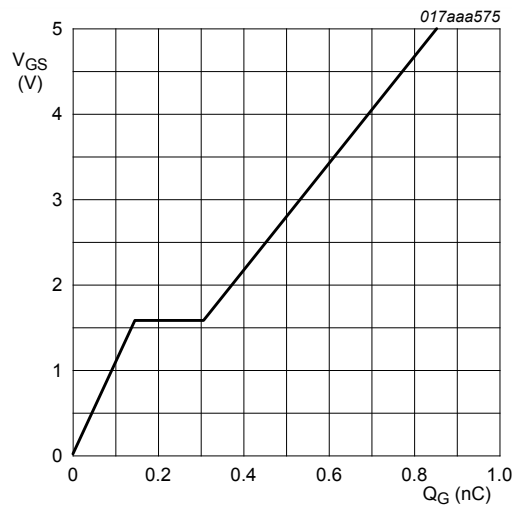


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$I_D = 0.5\text{ A}$; $V_{DS} = 15\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values

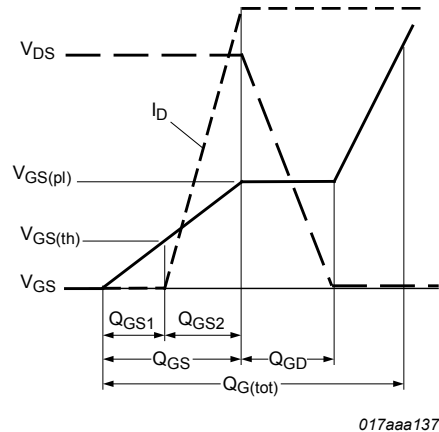
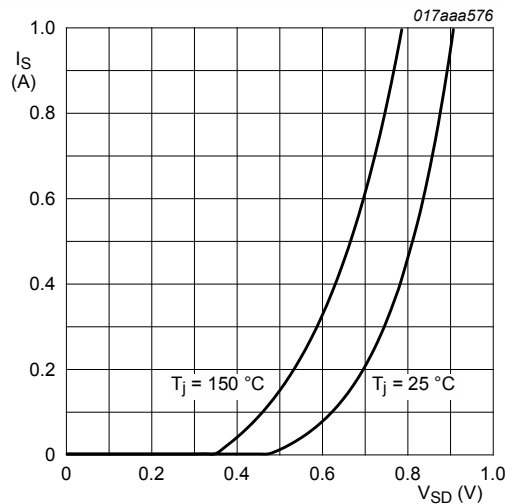


Fig. 15. Gate charge waveform definitions



$V_{GS} = 0\text{ V}$

Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

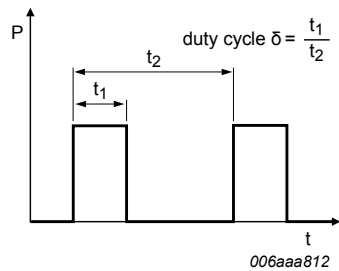
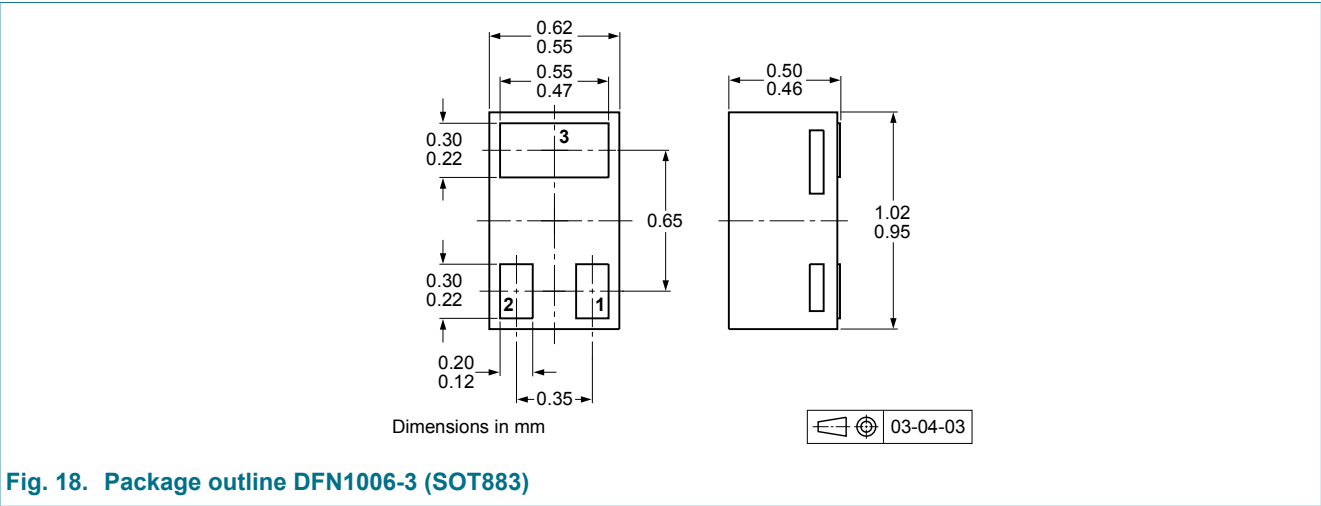
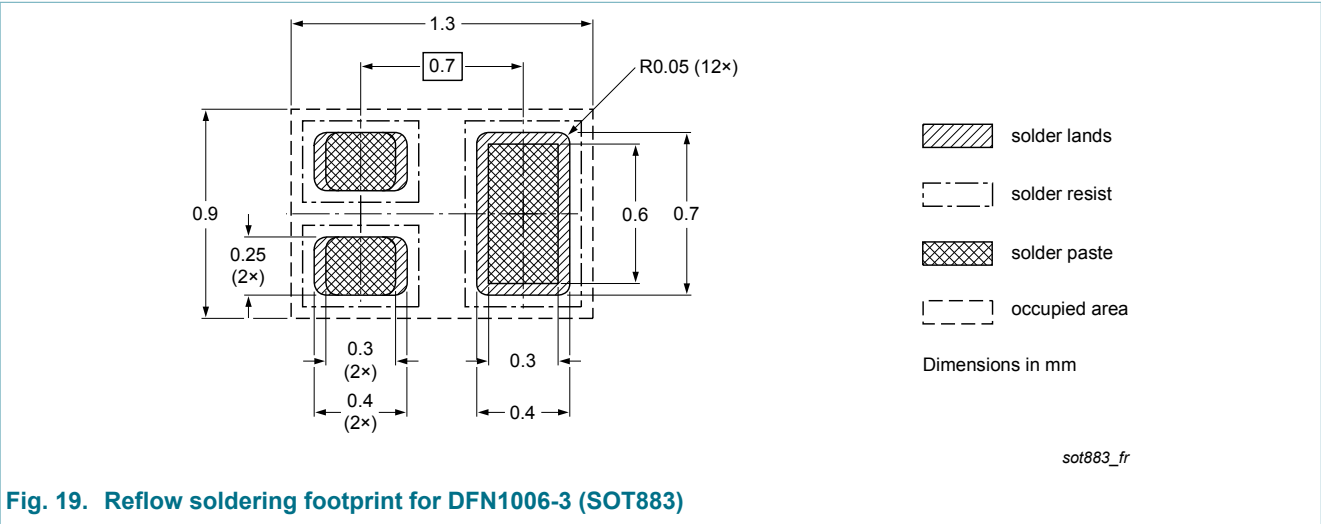


Fig. 17. Duty cycle definition

12. Package outline



13. Soldering



14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZ370UNE v.1	20140514	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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